

**Amendments to the claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

Claims 1 - 24: (canceled)

25. (original) A multilevel interconnect structure, comprising:

a semiconductor surface that has been provided with points of electrical contact in the surface of said surface;

a first layer of dielectric deposited on said semiconductor surface said first layer of dielectric containing a first network of trenches filled with air;

a second layer of dielectric deposited on said semiconductor surface said second layer of dielectric containing a second network of trenches filled with air whereby said second network of trenches is in physical contact with and intersects with said first network of trenches under an angle of known value; and

a layer of oxide deposited over the surface of said second layer of dielectric.

26. (original) The multilevel interconnect structure of claim 25 whereby furthermore a network of metal interconnect lines is created on the surface of said layer of oxide.

27. (original) The multilevel interconnect structure of claim 25 whereby furthermore said layer of oxide deposited over the surface of said second layer of dielectric trenches is extended in thickness by a measurable amount.

28. (original) The multilevel interconnect structure of claim 27 whereby furthermore a network of metal interconnect lines is created on the surface of said extended layer of oxide.